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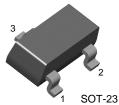
FAIRCHILD

SEMICONDUCTOR®

KSC3265

Low Frequency Amplifier

Complement to KSA1298



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

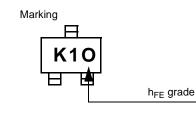
Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	30	V	
V _{CEO}	Collector-Emitter Voltage	25	V	
V _{EBO}	Emitter-Base Voltage	5	V	
lc	Collector Current	800	mA	
в	Base Current	160	mA	
Pc	Collector Power Dissipation	200	mW	
ТJ	Junction Temperature	150	°C	
Т _{STG}	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

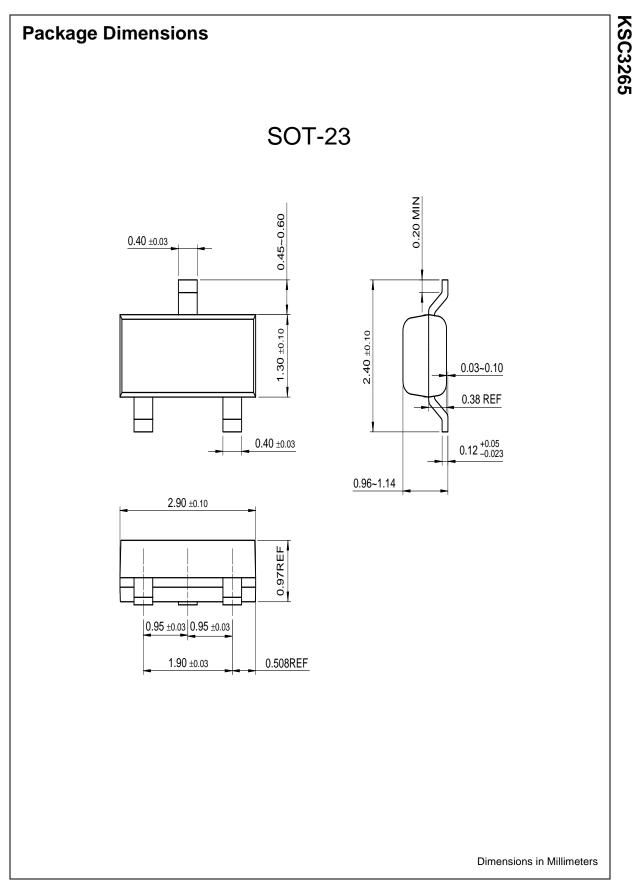
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, I _B =0	25			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =1mA, I _C =0	5			V
I _{CBO}	Collector Cut-off Current	V _{CB} =30V, I _E =0			100	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} =5V, I _C =0			100	nA
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} =1V, I _C =100mA V _{CE} =6V, I _C =800mA	100 40		320	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =500mA, I _B =20mA			0.4	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =1V, I _C =10mA	0.5		0.8	V
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =10mA		120		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		13		pF

h_{FE} Classification

Classification	0	Y
h _{FE}	100 ~ 200	160 ~ 320







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